

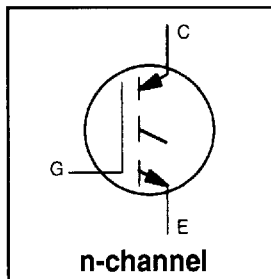
IRGPC50K

INSULATED GATE BIPOLAR TRANSISTOR

Short Circuit Rated
UltraFast IGBT

Features

- Short circuit rated - $10\mu\text{s}$ @ 125°C , $V_{\text{GE}} = 15\text{V}$
- Switching-loss rating includes all "tail" losses
- Optimized for high operating frequency (over 5kHz)
See Fig. 1 for Current vs. Frequency Curve



$$V_{\text{CES}} = 600\text{V}$$

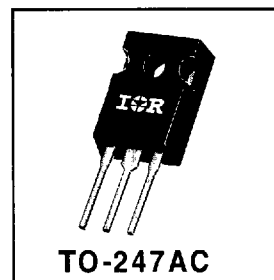
$$V_{\text{CE(sat)}} \leq 2.7\text{V}$$

$$@ V_{\text{GE}} = 15\text{V}, I_{\text{C}} = 30\text{A}$$

Description

Insulated Gate Bipolar Transistors (IGBTs) from International Rectifier have higher usable current densities than comparable bipolar transistors, while at the same time having simpler gate-drive requirements of the familiar power MOSFET. They provide substantial benefits to a host of high-voltage, high-current applications.

These new short circuit rated devices are especially suited for motor control and other applications requiring short circuit withstand capability.



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_{\text{C}} @ T_{\text{C}} = 25^\circ\text{C}$	Continuous Collector Current	52	A
$I_{\text{C}} @ T_{\text{C}} = 100^\circ\text{C}$	Continuous Collector Current	30	
I_{CM}	Pulsed Collector Current ①	100	
I_{LM}	Clamped Inductive Load Current ②	100	
t_{sc}	Short Circuit Withstand Time	10	μs
V_{GE}	Gate-to-Emitter Voltage	± 20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	20	mJ
$P_{\text{D}} @ T_{\text{C}} = 25^\circ\text{C}$	Maximum Power Dissipation	200	W
$P_{\text{D}} @ T_{\text{C}} = 100^\circ\text{C}$	Maximum Power Dissipation	52	
T_{J}	Operating Junction and	-55 to +150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta\text{JC}}$	Junction-to-Case	—	—	0.64	$^\circ\text{C/W}$
$R_{\theta\text{CS}}$	Case-to-Sink, flat, greased surface	—	0.24	—	
$R_{\theta\text{JA}}$	Junction-to-Ambient, typical socket mount	—	—	40	
Wt	Weight	—	6 (0.21)	—	g (oz)

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	20	—	—	V	$V_{GE} = 0V, I_C = 1.0A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temp. Coeff. of Breakdown Voltage	—	0.60	—	V/ $^\circ\text{C}$	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	2.1	2.7	V	$I_C = 30A, V_{GE} = 15V$
		—	2.6	—		$I_C = 52A, V_{GE} = 15V$
		—	2.3	—		$I_C = 30A, T_J = 150^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	5.5		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-14	—	mV/ $^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance ⑤	9.8	17	—	S	$V_{CE} = 100V, I_C = 30A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 600V$
		—	—	5000		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	120	200	nC	$I_C = 30A$
Q_{ge}	Gate - Emitter Charge (turn-on)	—	27	42		$V_{CC} = 400V$
Q_{gc}	Gate - Collector Charge (turn-on)	—	44	73		$V_{GE} = 15V$
$t_{d(on)}$	Turn-On Delay Time	—	35	—	ns	$T_J = 25^\circ\text{C}$
t_r	Rise Time	—	27	—		$I_C = 30A, V_{CC} = 480V$
$t_{d(off)}$	Turn-Off Delay Time	—	130	200		$V_{GE} = 15V, R_G = 5.0\Omega$
t_f	Fall Time	—	76	110		Energy losses include "tail"
E_{on}	Turn-On Switching Loss	—	0.9	—	mJ	See Fig. 9, 10, 11, 14
E_{off}	Turn-Off Switching Loss	—	0.5	—		
E_{ts}	Total Switching Loss	—	1.4	2.1		
t_{sc}	Short Circuit Withstand Time	10	—	—	μs	$V_{CC} = 360V, T_J = 125^\circ\text{C}$ $V_{GE} = 15V, R_G = 5.0\Omega$
$t_{d(on)}$	Turn-On Delay Time	—	32	—	ns	$T_J = 150^\circ\text{C}$
t_r	Rise Time	—	27	—		$I_C = 30A, V_{CC} = 480V$
$t_{d(off)}$	Turn-Off Delay Time	—	480	—		$V_{GE} = 15V, R_G = 5.0\Omega$
t_f	Fall Time	—	450	—		Energy losses include "tail"
E_{ts}	Total Switching Loss	—	2.8	—	mJ	See Fig. 10, 14
L_E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	2900	—	pF	$V_{GE} = 0V$
C_{oes}	Output Capacitance	—	220	—		$V_{CC} = 30V$
C_{res}	Reverse Transfer Capacitance	—	30	—		$f = 1.0MHz$

Notes:

① Repetitive rating; $V_{GE}=20V$, pulse width limited by max. junction temperature. (See fig. 13b)

③ Repetitive rating; pulse width limited by maximum junction temperature.

⑤ Pulse width 5.0 μs , single shot.

② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G = 5.0\Omega$, (See fig. 13a)

④ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.

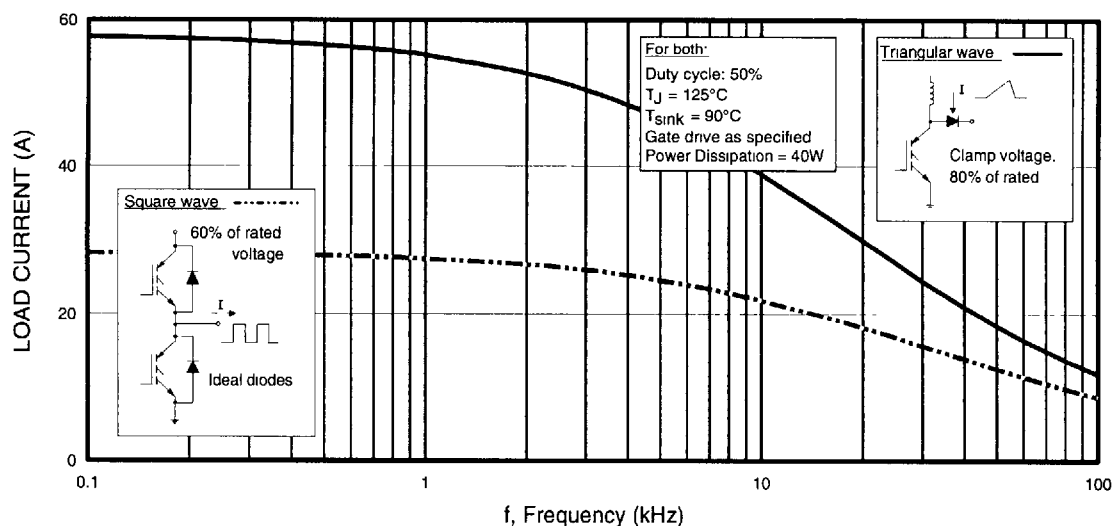


Fig. 1 - Typical Load Current vs. Frequency
(For square wave, $I = I_{\text{RMS}}$ of fundamental; for triangular wave, $I = I_{\text{PK}}$)

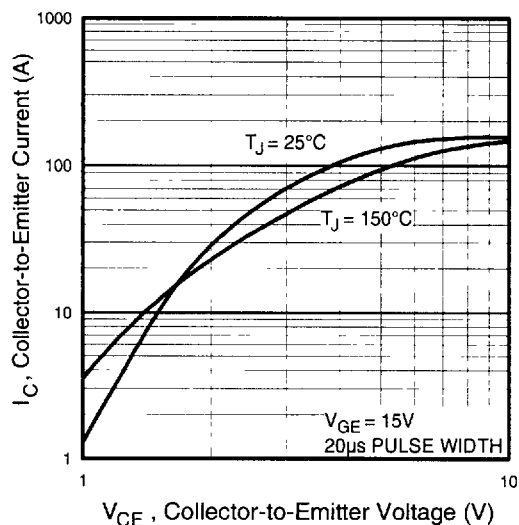


Fig. 2 - Typical Output Characteristics

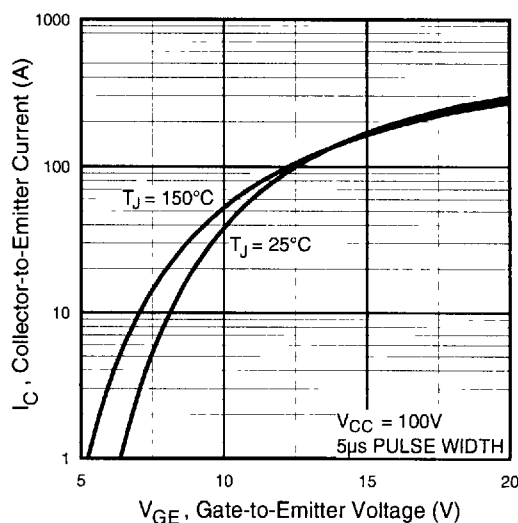


Fig. 3 - Typical Transfer Characteristics

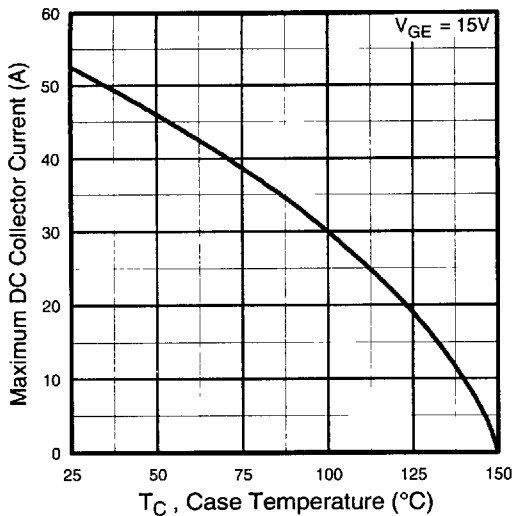


Fig. 4 - Maximum Collector Current vs. Case Temperature

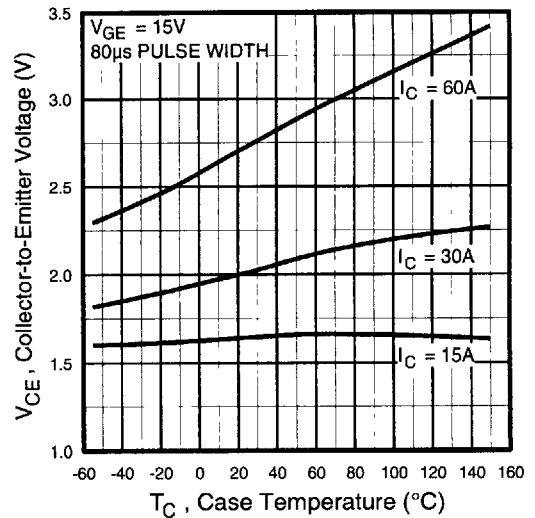


Fig. 5 - Collector-to-Emitter Voltage vs. Case Temperature

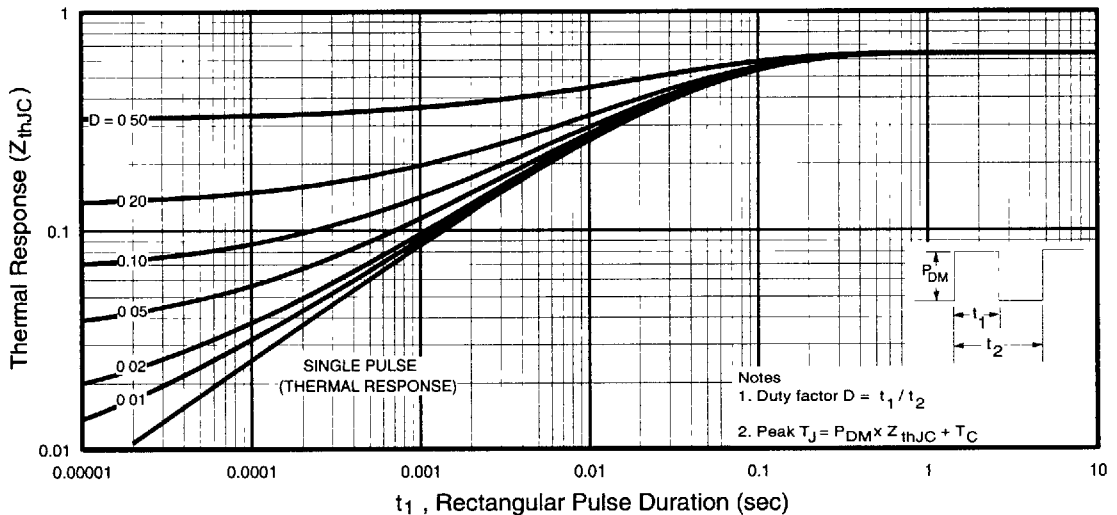


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

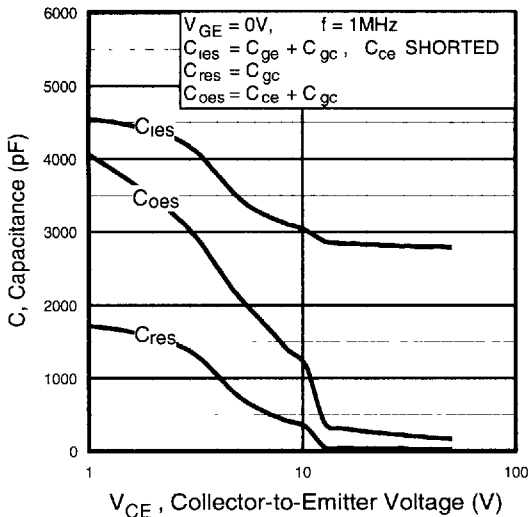


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

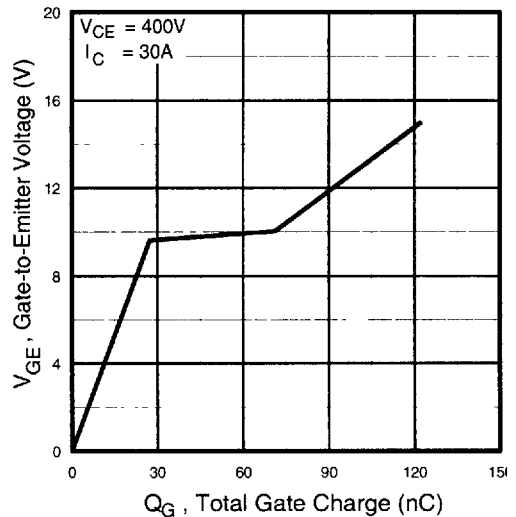


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

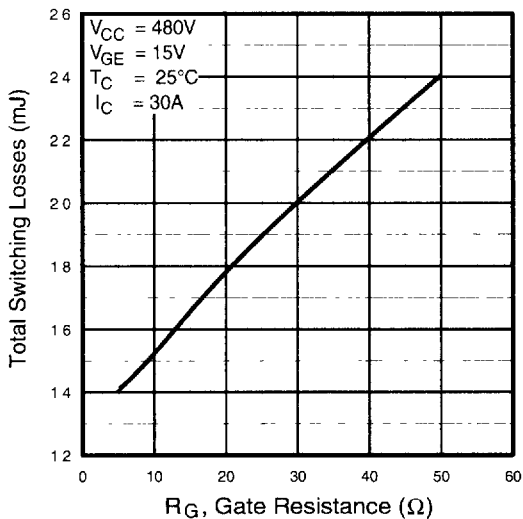


Fig. 9 - Typical Switching Losses vs. Gate Resistance

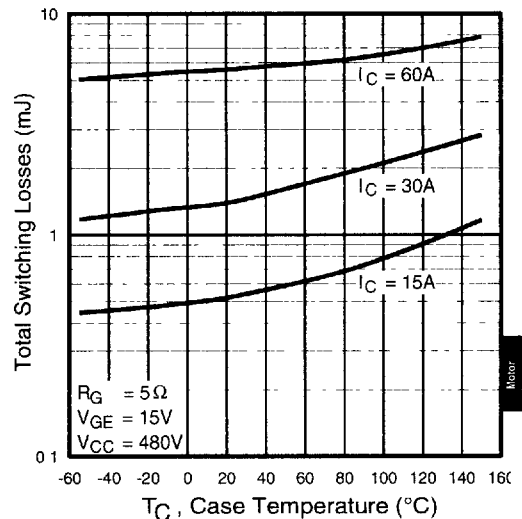


Fig. 10 - Typical Switching Losses vs. Case Temperature

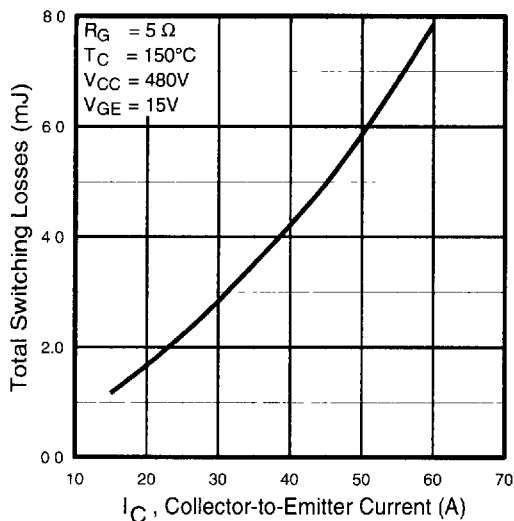


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

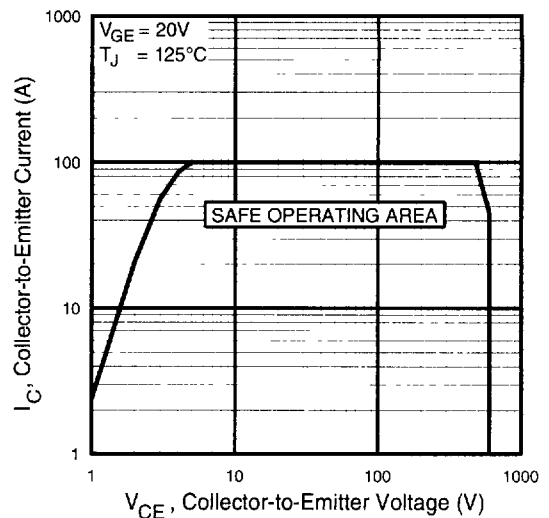


Fig. 12 - Turn-Off SOA

Refer to Section D for the following:

Appendix C: Section D - page D-5

Fig. 13a - Clamped Inductive Load Test Circuit

Fig. 13b - Pulsed Collector Current Test Circuit

Fig. 14a - Switching Loss Test Circuit

Fig. 14b - Switching Loss Waveform